

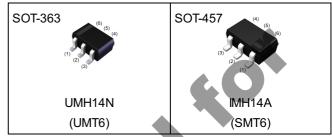
General purpose (dual digital transistor)

Parameter	DTr1 and DTr2
V _{CEO}	50V
I _C	100mA
R ₁	47kΩ

Features

- 1)Two DTC144T chips in a UMT or SMT package.
- 2)Mounting possible with UMT3 or SMT3 automatic mounting machines.
- 3)Transistor elements are independent, eliminating interference.
- 4) Mounting cost and area can be cut in half.

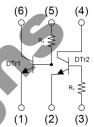
Outline



•Inner circuit

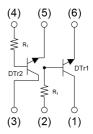
UMH14N

- (1) DTr1 Emitte
- (2) DTr2 Emitter
- (3) DTr2 Base
- (4) DTr2 Collector
- (5) DTr1 Base
- (6) DTr1 Collector



IMH14A

- (1) DTr1 Collector
- (2) DTr1 Base
- (3) DTr2 Collector
- (4) DTr2 Base
- (5) DTr2 Emitter
- (6) DTr1 Emitter



Application

INVERTER, INTERFACE, DRIVER

Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
UMH14N	SOT-363 (UMT6)	2021	TR	180	8	3000	H14
IMH14A	SOT-457 (SMT6)	2928	T108	180	8	3000	H14

● Absolute maximum ratings (T_a = 25°C)

<For DTr1 and DTr2 in common>

Parameter			Symbol	Values	Unit	
Collector-base voltage			V_{CBO}	50	V	
Collector-emitter voltage			V_{CEO}	50	V	
Emitter-base voltage	mitter-base voltage V _{EE}		V _{EBO}	5	V	
Collector current			I _C	100	mA	
Davis and in a line of the co	UMH14N		P _D *1*2	150	mW/Tota	
Power dissipation	IMH14A		P _D *1*3	300		
Junction temperature			T _j	150	°C	
Range of storage temperature			T _{stg}	-55 to +150	°C	

● Electrical characteristics (T_a = 25°C)

<For DTr1 and DTr2 in common>

				6		
● Electrical characteristics (T _a <for and="" comm<="" dtr1="" dtr2="" in="" td=""><td>•</td><td></td><td></td><td></td><td></td><td></td></for>	•					
Parameter	Symbol	Conditions	Min.	Values Typ.	Max.	Unit
Collector-base breakdown voltage	BV _{CBO}	l _C = 50μA	50	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA	50	-	-	V
Emitter-base breakdown voltage	BV _{EBO}	Ι _Ε = 50μΑ	5	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = 50V	-	-	500	nA
Emitter cut-off current	I _{EBO}	V _{EB} = 4V	-	-	500	nA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 10mA, I _B = 1mA	-	-	300	mV
DC current gain	h _{FE}	V _{CE} = 5V, I _C = 1mA	100	250	600	-
Input resistance	R ₁	-	32.9	47	61.1	kΩ
Transition frequency	f _T *4	V _{CE} = 10V, I _E = -5mA, f = 100MHz	-	250	-	MHz

^{*1} Each terminal mounted on a reference land.

^{*2 120}mW per element must not be exceeded.

^{*3 200}mW per element must not be exceeded.

^{*4} Characteristics of built-in transistor.

● Electrical characteristic curves (T_a = 25°C)

<For DTr1 and DTr2 in common>

Fig.1 Grounded Emitter Propagation
Characteristics

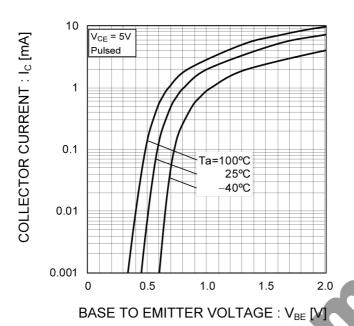


Fig.2 Grounded Emitter Output Characteristics

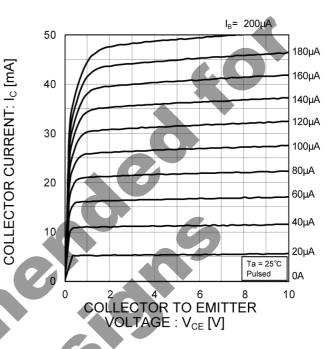


Fig.3 DC Current Gain vs. Collector Current

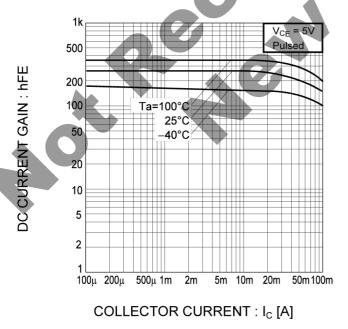
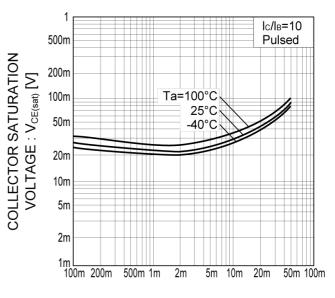
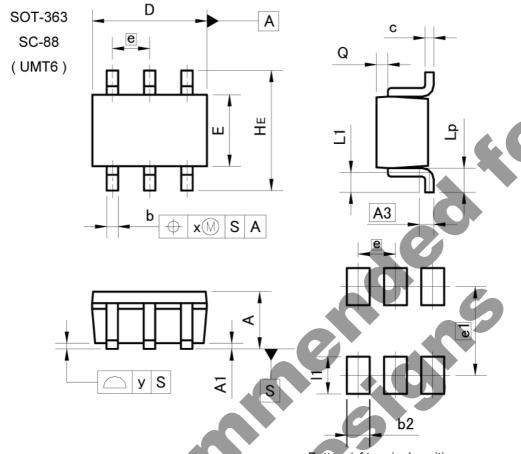


Fig.4 Collector-Emitter Saturation Voltage vs. Collector Current



COLLECTOR CURRENT : I_C [A]

Dimensions



Pattern of termina	al position	areas
[Not a pattern of	soldering	pads]
	•	

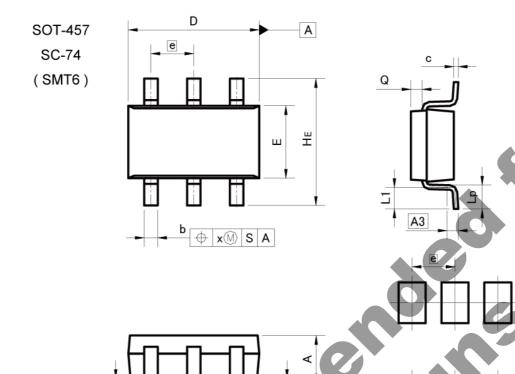
DIM	DIM MILIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	0.80	1.00	0.031	0.039
(A1	0.00	0.10	0.000	0.004
A3	0.1	25	0.0	10
b	0.15	0.30	0.006	0.012
С	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
е	0.	65	0.026	
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.020
Lp	0.25	0.55	0.010	0.022
Q	0.10	0.30	0.004	0.012
х	-	0.10	s -7	0.004
У	-	0.10	-	0.004

DIM	MILIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
b2	- 7	0.40	-	0.016	
e1	1.55		0.0	61	
11	_	0.65	-	0.026	

Dimension in mm/inches



Dimensions



Pattern of terminal position areas [Not a pattern of soldering pads]

e1

DIM	MILIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.00	1.30	0.039	0.051
A1	0.00	0.10	0.000	0.004
A3	0.:	25	0.0	10
b	0.25	0.40	0.010	0.016
С	0.09	0.25	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
е	0.9	95	0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
х		0.20		0.008
У	- -2	0.10		0.004

S

DIM	MILIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
b2		0.60	-	0.024	
e1	2.	10	0.0	083	
11	>	0.90	-	0.035	

Dimension in mm/inches

Notes

- 1) The information contained herein is subject to change without notice.
- 2) Before you use our Products, please contact our sales representative and verify the latest specifica-
- Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors.

 Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM
- 4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.
- 5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.
- 6) The Products are intended for use in general electronic equipment (i.e. AV/OA devices, communication, consumer systems, gaming/entertainment sets) as well as the applications indicated in this document.
- 7) The Products specified in this document are not designed to be radiation tolerant.
- 8) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative: fransportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, servers, solar cells, and power transmission systems.
- Do not use our Products in applications requiring extremely high reliability, such as aerospace equipment, nuclear power control systems, and submarine repeaters.
- 10) ROHM shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions and specifications contained herein.
- 11) ROHM has used reasonable care to ensur the accuracy of the information contained in this document. However, ROHM does not warrants that such information is error-free, and ROHM shall have no responsibility for any damages arising from any inaccuracy or misprint of such information.
- Please use the Products in accordance with any applicable environmental laws and regulations, such as the RoHS Directive. For more details, including RoHS compatibility, please contact a ROHM sales office. ROHM shall have no responsibility for any damages or losses resulting non-compliance with any applicable laws or regulations.
- 13) When providing our Products and technologies contained in this document to other countries, you must abide by the procedures and provisions stipulated in all applicable export laws and regulations, including without limitation the US Export Administration Regulations and the Foreign Exchange and Foreign Trade Act.
- 14) This document, in part or in whole, may not be reprinted or reproduced without prior consent of ROHM



Thank you for your accessing to ROHM product informations.

More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/

www.rohm.com © 2015 ROHM Co., Ltd. All rights reserved.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - Pre-Biased category:

Click to view products by ROHM manufacturer:

Other Similar products are found below:

RN1607(TE85L,F) DTA124GKAT146 DTA144WETL DTA144WKAT146 DTC113EET1G DTC115TETL DTC115TKAT146

DTC124TETL DTC144ECA-TP DTC144VUAT106 MUN5241T1G BCR158WH6327XTSA1 NSBA114TDP6T5G NSBA143ZF3T5G

NSBC114YF3T5G NSBC123TF3T5G SMUN5235T1G SMUN5330DW1T1G SSVMUN5312DW1T2G RN1303(TE85L,F)

RN4605(TE85L,F) TTEPROTOTYPE79 DDTC114EUAQ-7-F EMH15T2R SMUN2214T3G SMUN5335DW1T1G NSBC114TF3T5G

NSBC143ZPDP6T5G NSVMUN5113DW1T3G SMUN5230DW1T1G SMUN5133T1G SMUN2214T1G DTC114EUA-TP

NSBA144EF3T5G NSVDTA114EET1G 2SC2223-T1B-A 2SC3912-TB-E SMUN5237DW1T1G SMUN5213DW1T1G

SMUN5114DW1T1G SMUN2111T1G NSVDTC144EM3T5G DTC124ECA-TP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G

DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G NSVMUN2237T1G